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Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET

PDTC124T series NPN resistor-equipped transistors; R1 = 22 k Ω , R2 = open

Product data sheet Supersedes data of 2004 Apr 06 2004 Aug 13



NPN resistor-equipped transistors; R1 = 22 k Ω , R2 = open

PDTC124T series

FEATURES

- Built-in bias resistors
- · Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

APPLICATIONS

- · General purpose switching and amplification
- · Inverter and interface circuits
- Circuit driver.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V_{CEO}	collector-emitter voltage	_	50	V
Io	output current (DC)	_	100	mA
R1	bias resistor	22	-	kΩ
R2	open	_	_	_

DESCRIPTION

NPN resistor-equipped transistor (see "Simplified outline, symbol and pinning" for package details).

PRODUCT OVERVIEW

TYPE NUMBER	PAC	KAGE	MARKING CODE	DND COMPLEMENT
TYPE NUMBER	PHILIPS	EIAJ	MARKING CODE	PNP COMPLEMENT
PDTC124TE	SOT416	SC-75	41	PDTA124TE
PDTC124TEF	SOT490	SC-89	35	PDTA124TEF
PDTC124TK	SOT346	SC-59	50	PDTA124TK
PDTC124TM	SOT883	SC-101	DY	PDTA124TM
PDTC124TS	SOT54 (TO-92)	SC-43	TC124T	PDTA124TS
PDTC124TT	SOT23	_	*45 ⁽¹⁾	PDTA124TT
PDTC124TU	SOT323	SC-70	*50 ⁽¹⁾	PDTA124TU

Note

^{1. * =} p: Made in Hong Kong.

^{* =} t: Made in Malaysia.

^{* =} W: Made in China.

NPN resistor-equipped transistors; R1 = 22 k Ω , R2 = open

PDTC124T series

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	CIMPLIFIED OUTLINE AND CVMDOL		PINNING
TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PIN	DESCRIPTION
PDTC124TS	1 1 2 1 R1 3 3 MAM361	1 2 3	base collector emitter
PDTC124TE PDTC124TEF PDTC124TK PDTC124TT PDTC124TU	3 1 R1 1 R1 2 Top view MDB270	1 2 3	base emitter collector
PDTC124TM	2 R1 3 1 Bottom view MHC507	1 2 3	base emitter collector

NPN resistor-equipped transistors; R1 = 22 k Ω , R2 = open

PDTC124T series

ORDERING INFORMATION

TYPE NUMBER		PACKAGE	
ITPE NUMBER	NAME	DESCRIPTION	VERSION
PDTC124TE	_	plastic surface mounted package; 3 leads	SOT416
PDTC124TEF	_	plastic surface mounted package; 3 leads	SOT490
PDTC124TK	_	plastic surface mounted package; 3 leads	SOT346
PDTC124TM	_	leadless ultra small plastic package; 3 solder lands; body $1.0 \times 0.6 \times 0.5$ mm	SOT883
PDTC124TS	_	plastic single-ended leaded (through hole) package; 3 leads	SOT54
PDTC124TT	_	plastic surface mounted package; 3 leads	SOT23
PDTC124TU	_	plastic surface mounted package; 3 leads	SOT323

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	50	V
V _{CEO}	collector-emitter voltage	open base	_	50	V
V _{EBO}	emitter-base voltage	open collector	_	5	V
Io	output current (DC)		_	100	mA
I _{CM}	peak collector current		_	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C			
	SOT54	note 1	_	500	mW
	SOT23	note 1	_	250	mW
	SOT346	note 1	_	250	mW
	SOT323	note 1	_	200	mW
	SOT490	notes 1 and 2	_	250	mW
	SOT883	notes 2 and 3	_	250	mW
	SOT416	note 1	_	150	mW
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Notes

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60 μm copper strip line.

2004 Aug 13

NPN resistor-equipped transistors; R1 = 22 k Ω , R2 = open

PDTC124T series

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	in free air		
	SOT54	note 1	250	K/W
	SOT23	note 1	500	K/W
	SOT346	note 1	500	K/W
	SOT323	note 1	625	K/W
	SOT490	notes 1 and 2	500	K/W
	SOT883	notes 2 and 3	500	K/W
ı	SOT416	note 1	833	K/W

Notes

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60 μ m copper strip line.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	V _{CB} = 50 V; I _E = 0 A	_	_	100	nA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}$	_	_	1	μА
		$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}; T_{j} = 150 ^{\circ}\text{C}$	_	_	50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$	_	_	100	nA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 1 \text{ mA}$	100	_	_	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	_	_	150	mV
R1	input resistor		15.4	22	28.6	kΩ
C _c	collector capacitance	$I_E = I_e = 0 \text{ A}; V_{CB} = 10 \text{ V};$ f = 1 MHz	_	_	2.5	pF

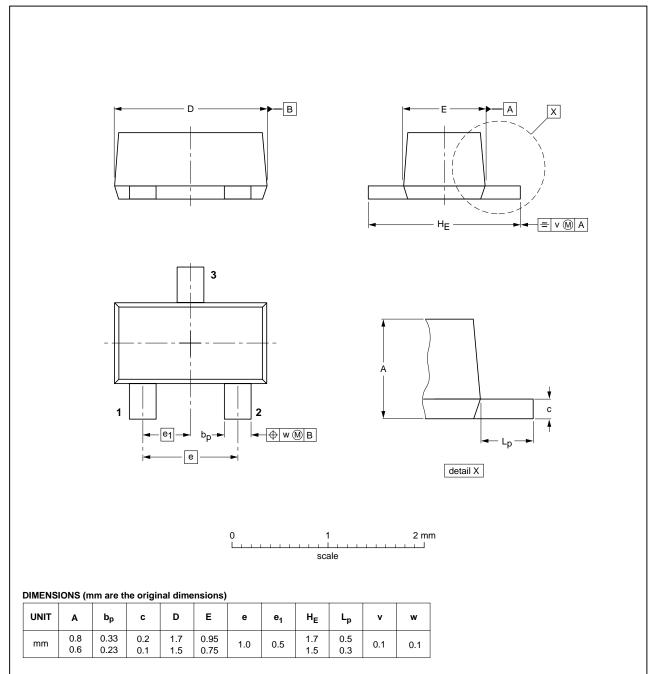
NPN resistor-equipped transistors; R1 = 22 k Ω , R2 = open

PDTC124T series

PACKAGE OUTLINES

Plastic surface-mounted package; 3 leads

SOT490



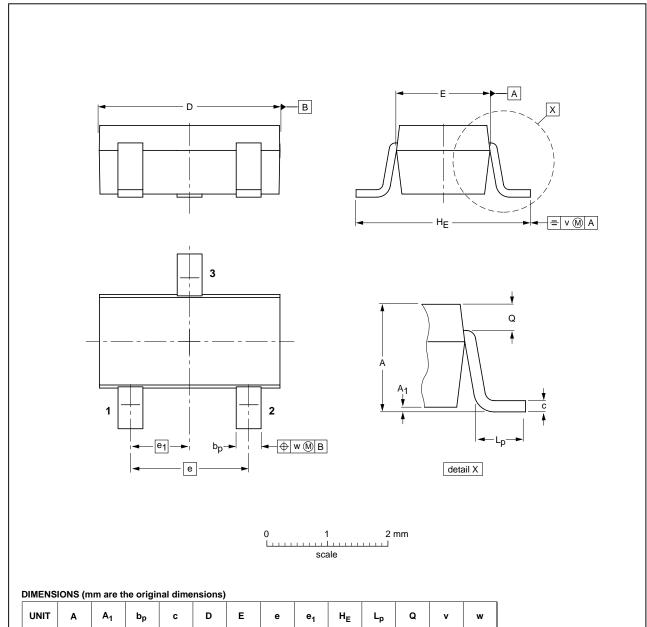
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IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
		SC-89			05-07-28 06-03-16
	IEC		IEC JEDEC JEITA	IEC JEDEC JEITA	IEC JEDEC JEITA PROJECTION

NPN resistor-equipped transistors; R1 = 22 k Ω , R2 = open

PDTC124T series

Plastic surface-mounted package; 3 leads

SOT346



OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION		
SOT346		TO-236	SC-59A		-04-11-11 06-03-16	

7

0.6

0.33

0.2

0.2

2004 Aug 13

0.1

0.013

0.50

0.35

0.26

1.3

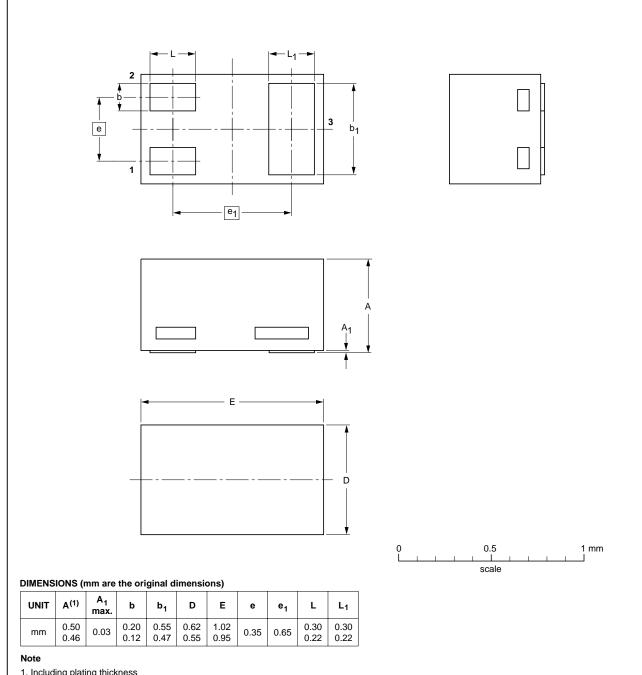
1.0

NPN resistor-equipped transistors; $R1 = 22 \text{ k}\Omega$, R2 = open

PDTC124T series

Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

SOT883



1. Including plating thickness

OUTLINE		REFER	ENCES	EUROPEAN ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT883			SC-101			03-02-05 03-04-03	

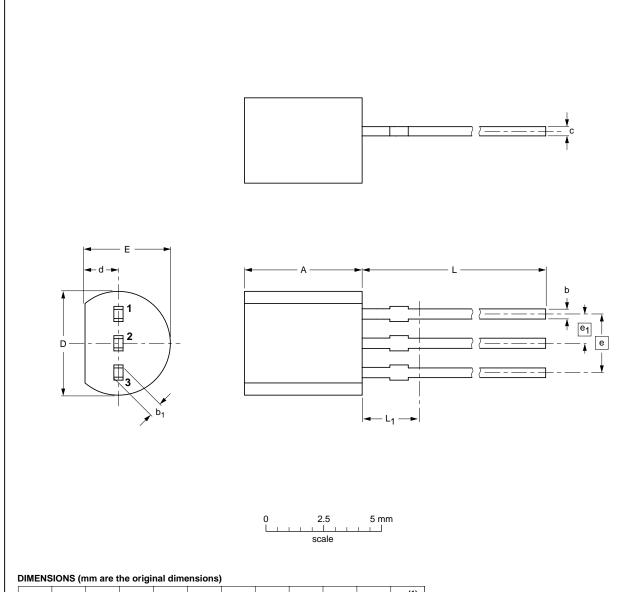
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NPN resistor-equipped transistors; R1 = 22 k Ω , R2 = open

PDTC124T series

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



UNIT	Α	b	b ₁	С	D	d	E	е	e ₁	L	L ₁ ⁽¹⁾ max.	
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5	

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

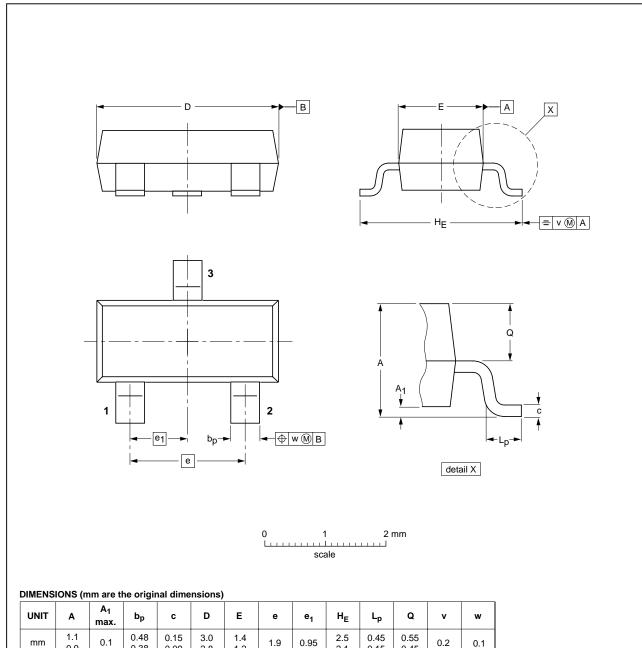
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VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT54		TO-92	SC-43A		04-06-28 04-11-16	

NPN resistor-equipped transistors; R1 = 22 k Ω , R2 = open

PDTC124T series

Plastic surface-mounted package; 3 leads

SOT23



OUTLINE		EUROPEAN	ICCUE DATE				
VERSION	VERSION IEC		JEDEC JEITA		PROJECTION	ISSUE DATE	
SOT23		TO-236AB				-04-11-04- 06-03-16	

2004 Aug 13 10

0.38

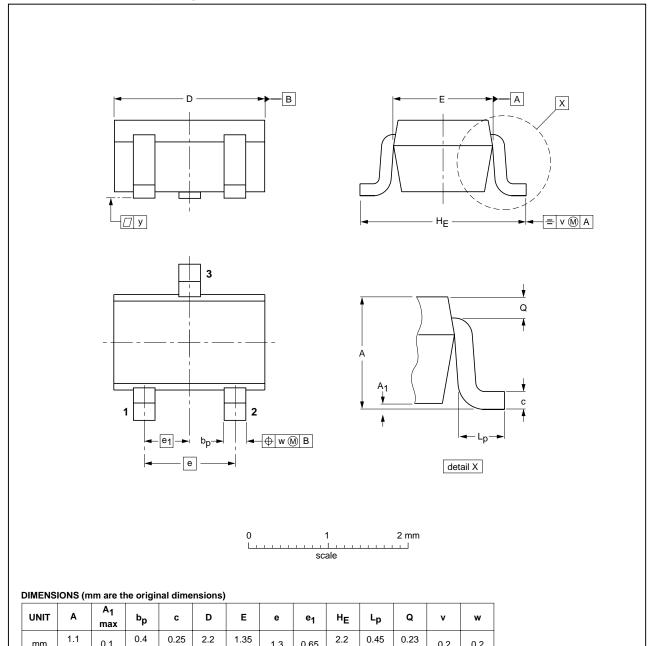
0.9

NPN resistor-equipped transistors; $R1 = 22 \text{ k}\Omega$, R2 = open

PDTC124T series

Plastic surface-mounted package; 3 leads

SOT323



OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEDEC JEITA		PROJECTION	
SOT323			SC-70			-04-11-04 06-03-16

0.2

0.2

1.3

0.65

2004 Aug 13 11

0.3

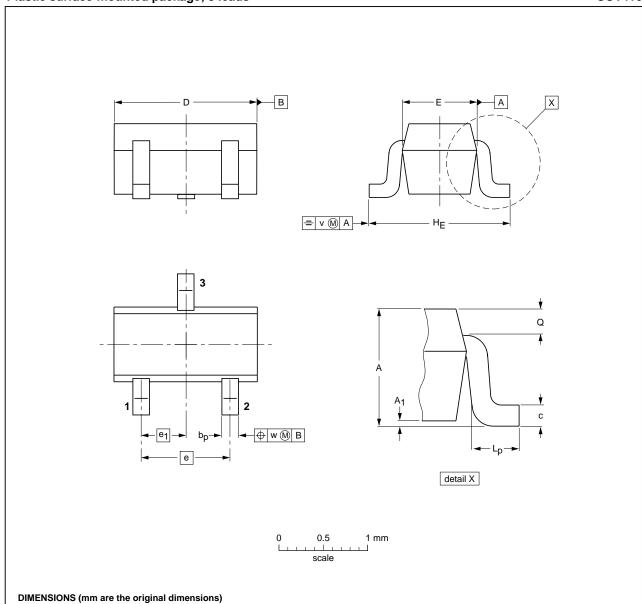
mm

NPN resistor-equipped transistors; R1 = 22 k Ω , R2 = open

PDTC124T series

Plastic surface-mounted package; 3 leads

SOT416



UNIT	Α	A ₁ max	bp	С	D	E	е	e ₁	HE	Lp	Q	v	w
mm	0.95 0.60	0.1	0.30 0.15	0.25 0.10	1.8 1.4	0.9 0.7	1	0.5	1.75 1.45	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE		EUROPEAN	ISSUE DATE				
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT416			SC-75			04-11-04 06-03-16	

NPN resistor-equipped transistors; R1 = 22 k Ω , R2 = open

PDTC124T series

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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- 2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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SMUN5114DW1T1G SMUN2111T1G NSVDTC144EM3T5G DTC124ECA-TP DTC123TM3T5G DTA114ECA-TP DTA113EM3T5G

DCX115EK-7-F DTC113EM3T5G NSVMUN5135DW1T1G NSVMUN2237T1G